

ABSTRACT

METHOD FOR EVALUATING LITHOGRAPHY SYSTEM, METHOD FOR ADJUSTING SUBSTRATE-PROCESSING APPARATUS, LITHOGRAPHY SYSTEM, AND EXPOSURE APPARATUS

When the ordinary exposure is performed, a wafer, to which a photoresist is applied by a resist coater, is transported onto a wafer stage of a projection exposure apparatus to perform the exposure, followed by development by a developing apparatus. When the characteristic is evaluated, respective shot areas on the wafer applied with the photoresist are exposed with an image of a predetermined evaluating mark in a narrow area in an effective field of a projection optical system of the projection exposure apparatus. The characteristic of the resist coater or the developing apparatus is evaluated by detecting a state of a resist pattern after the development. When the image formation characteristic of the projection exposure apparatus is evaluated, the wafer is exposed with images of a plurality of predetermined evaluating marks in a wide area in the effective field. The respective characteristics of the resist coater, the exposure apparatus, and the developing apparatus for constructing a lithography system can be evaluated respectively independently.

(Fig. 1)